IN THE CLAIMS:

This listing of the claims replaces all prior versions and listings of the claims.

1. (Previously presented) An evaluation method for polycrystalline silicon which is used as a material for pulling single crystal silicon, comprising the steps of:

immersing a predetermined amount of the polycrystalline silicon in a predetermined amount of an agent contained in a vessel, which agent is capable of dissolving the polycrystalline silicon; and

placing a measuring device in the agent having the polycrystalline silicon dissolved therein to count the number of foreign particles dispersed in the agent.

2. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 1, wherein the measuring device is a particle counter.

3. (Original) An evaluation method for polycrystalline silicon as set forth in claim 1, wherein the polycrystalline silicon immersed in the agent is aggregated or in pellet shape.

4. (Original) An evaluation method for polycrystalline silicon as set forth in claim 2, wherein the polycrystalline silicon immersed in the agent is aggregated or in pellet shape.

5. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 1, further comprising the step of:

analyzing the composition of the foreign particles.

6. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 2, further comprising the step of:

analyzing the composition of the foreign particles.

7. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 1, wherein said foreign particles cause crystal defects.

8. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 5, wherein the analysis is carried out using scanning electron microscopy or energy dispersive X-ray spectroscopy.

9. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 1, further comprising the step of:

subjecting the agent to a circulation filtering process prior to the immersion of the polycrystalline silicon in the agent.

10. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 2, further comprising the step of:

subjecting the agent to a circulation filtering process prior to the immersion of the polycrystalline silicon in the agent.

11. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 3, further comprising the step of:

subjecting the agent to a circulation filtering process prior to the immersion of the polycrystalline silicon in the agent.

12. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 4, further comprising the step of:

subjecting the agent to a circulation filtering process prior to the immersion of the polycrystalline silicon in the agent.

13. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 5, further comprising the step of:

subjecting the agent to a circulation filtering process prior to the immersion of the polycrystalline silicon in the agent.

14. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 6, further comprising the step of:

subjecting the agent to a circulation filtering process prior to the immersion of the polycrystalline silicon in the agent.

15. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 7, further comprising the step of:

subjecting the agent to a circulation filtering process prior to the immersion of the

polycrystalline silicon in the agent.

16. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 8, further comprising the step of:

subjecting the agent to a circulation filtering process prior to the immersion of the polycrystalline silicon in the agent.

17. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 1, wherein counting the number of foreign particles includes using a measuring device.

18. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 17, wherein the measuring device is a particle counter.

19. (Previously presented) An evaluation method for polycrystalline silicon as set forth in claim 1, wherein the agent is hydrofluoric acid and nitric acid.

20. (Previously presented) An evaluation method according to claim 1, wherein said agent is an etchant.